L Number	Hits	Search Text	DB	Time stamp
15	7	(boe or buffer\$3 near2 oxid\$2 near2 etch\$4) same ("h.sub.2so.sub.4" or h2s04 or sulfuric) same combination	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/28 10:25
16	90	(boe or buffer\$3 near2 oxid\$2 near2 etch\$4) same ("h.sub.2so.sub.4" or h2s04 or sulfuric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/28 10:26
17	20	(boe or buffer\$3 near2 oxid\$2 near2 etch\$4) same ("h.sub.2so.sub.4" or h2s04 or sulfuric) same (HF)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/28 10:32
_	118	(contact near5 plug same (silicon or si) and temperature near3 (deposit\$4 or grow\$4) near10 (silicon or si)) and (lpcvd or low near2 pressure near2 chemical near2 vapor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/04 16:19
_	14	_ · · · · · · · · · · · · · · · · · · ·	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/04 16:37
_	84	selectiv\$4 near3 epitax\$4 near10 (silicon or si or polysilicon) and (low near2 pressure near3 chemical near2 vapor or lpcvd) and two near10 (deposit\$4 or grow\$4 or epitax\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/04 16:51
_	38	((silicon or si) near4 amorphous or polysilicon) same plug near5 contact same (low near4 pressure or lpcvd) same temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/04 17:00
-	24	((silicon or si) near4 amorphous or polysilicon) near10 plug near5 contact same (low near4 pressure or lpcvd) same temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/04 17:00
_	81	contact near5 plug same (single or epitax\$4) near5 (si or silicon) same (amorphous near4 (silicon) or poly or poly\$1si or poly\$1silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/05 14:59
-	40	(contact near5 plug same (single or epitax\$4) near5 (si or silicon) same (amorphous near4 (silicon) or poly or poly\$1si or poly\$1silicon)) and (lpcvd or low near3 pressure near3 chemical near2 vapor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/05 15:18
-	10	(lpcvd or low near3 pressure near3 chemical near2 vapor) and selective near4 (epitax\$4 or grow\$4 or deposit\$4) same contact near4 plug same (single or epitax\$4) near5 (si or silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/05 15:51
-	53		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/05 15:55
-	18	(lpcvd or low near3 pressure near3 chemical near2 vapor) and contact near4 plug near10 (silicon or si) and flow near3 rate same temperature same silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/05 15:56

_	58	(lpcvd or low near2 pressure near2	USPAT;	2003/06/05
		chemical) near10 (silicon or si) same	US-PGPUB;	16:24
		plug same temperature	EPO; JPO;	
			DERWENT;	
1_	3	(lpcvd or low near2 pressure near2	IBM_TDB USPAT;	2003/06/05
		chemical) near10 (silicon or si) near10	US-PGPUB;	16:26
		(crystal\$4 or crystallin\$4) same plug	EPO; JPO;	
		same temperature	DERWENT;	
	60	(1	IBM_TDB	2003/06/05
-	62	(lpcvd or low near2 pressure near2 chemical) near10 (silicon or si) near10	USPAT; US-PGPUB;	16:26
		(crystal\$4 or crystallin\$4) same	EPO; JPO;	10.20
		temperature	DERWENT;	
			IBM_TDB	0000/06/05
-	6	(lpcvd or low near2 pressure near2 chemical) near10 (silicon or si) near10	USPAT; US-PGPUB;	2003/06/05 16:31
		(crystal\$4 or crystallin\$4) near10	EPO; JPO;	10.51
		select\$5 same temperature	DERWENT;	
			IBM_TDB	
-	28		USPAT;	2003/06/05
		chemical) same (silicon or si) near10 (crystal\$4 or crystallin\$4) near10	US-PGPUB; EPO; JPO;	16:35
		select\$5 same temperature	DERWENT;	
		_	IBM_TDB	
-	84	1 1 1 2	USPAT;	2003/06/05
		chemical) and (silicon or si) near10 (crystal\$4 or crystallin\$4) near10	US-PGPUB; EPO; JPO;	16:57
		select\$5 near4 (epitax\$4 or grow\$4 or	DERWENT;	
		deposit\$4) same temperature	IBM_TDB	
-	56	(NF3 or "NF.sub.3") near10 (o2 or oxygen	USPAT;	2003/06/06
		or "o.sub.2") near5 plasma same clean\$4	US-PGPUB;	10:22
			EPO; JPO; DERWENT;	
			IBM TDB	
_	5	(NF3 or "NF.sub.3") near10 (o2 or oxygen	USPAT;	2003/06/06
		or "o.sub.2") near5 plasma same clean\$4	US-PGPUB;	11:10
		same (contact or plug)	EPO; JPO; DERWENT;	
	1		IBM TDB	
-	4	clean\$4 same (contact or plug) same (boe	USPAT;	2003/06/06
		or buffer\$3 near2 oxid\$2 near2 etch\$4)	US-PGPUB;	09:43
		same ("h.sub.2so.sub.4" or h2s04 or	EPO; JPO;	
		sulfuric)	DERWENT; IBM TDB	
_	30	clean\$4 same (boe or buffer\$3 near2	USPAT;	2003/07/28
		oxid\$2 near2 etch\$4) same	US-PGPUB;	10:18
		("h.sub.2so.sub.4" or h2s04 or sulfuric)	EPO; JPO;	
			DERWENT; IBM TDB	
_	. 0	 wet near4 etch\$4 same (dry or plasma)	USPAT;	2003/06/06
		near3 etch\$4 same clean\$4 same (contact	US-PGPUB;	09:49
		or plug or via) same (NF3 or "nf.sub.3")	EPO; JPO;	
			DERWENT;	
_	9	 wet near4 etch\$4 same (dry or plasma)	USPAT;	2003/06/06
1		near3 etch\$4 same clean\$4 same (contact	US-PGPUB;	09:50
	1	or plug or via) same bak\$4	EPO; JPO;	
1			DERWENT;	
1_	25	((NF3 or "NF.sub.3") near10 (o2 or oxygen	IBM_TDB USPAT;	2003/06/06
		or "o.sub.2") near5 plasma) and (boe or	US-PGPUB;	09:53
1		buffer\$3 near2 oxid\$3 near3 etch\$4)	EPO; JPO;	
1			DERWENT;	
_	128	(boe or buffer\$3 near2 oxid\$3 near3	IBM_TDB USPAT;	2003/06/06
	128	etch\$4) same (h2so4 or "h.sub.2so.sub.4"	US-PGPUB;	09:59
		or sulfur\$3)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	

_	18	((boe or buffer\$3 near2 oxid\$3 near3	USPAT;	2003/06/06
		etch\$4) same (h2so4 or "h.sub.2so.sub.4" or sulfur\$3)) same (contact or via or	US-PGPUB; EPO; JPO;	09:57
		plug or trench)	DERWENT;	
		prug or cremen,	IBM TDB	
-	34	(boe or buffer\$3 near2 oxid\$3 near3	USPĀT;	2003/06/06
		etch\$4) same (h2so4 or "h.sub.2so.sub.4"	US-PGPUB;	10:00
		or sulfur\$3) same clean\$4	EPO; JPO;	
			DERWENT; IBM TDB	
	30	(NF3 or "NF.sub.3" or fluor\$4) near10 (o2	USPAT;	2003/06/06
-	39	or oxygen or "o.sub.2") near5 (plasma or	US-PGPUB;	10:52
		dry) same clean\$4 same (via or hole or	EPO; JPO;	20102
		contact or plug or trench)	DERWENT;	
			IBM_TDB	
-	95	((NF3 or "NF.sub.3" or fluor\$4) near10	USPAT;	2003/06/06
		(o2 or oxygen or "o.sub.2") near5 (plasma	US-PGPUB;	10:54
	1	or dry) same clean\$4 and (via or hole or	EPO; JPO; DERWENT;	
		contact or plug or trench)) not ((NF3 or "NF.sub.3" or fluor\$4) near10 (o2 or	IBM TDB	
		oxygen or "o.sub.2") near5 (plasma or	12122	
		dry) same clean\$4 same (via or hole or		
		contact or plug or trench)) not (((NF3 or		
		"NF.sub.3") near10 (o2 or oxygen or		
		"o.sub.2") near5 plasma) and (boe or		
	7.	buffer\$3 near2 oxid\$3 near3 etch\$4))	IISDAT.	2003/06/06
-	71	((NF3 or "NF.sub.3" or fluor\$4) near10 (o2 or oxygen or "o.sub.2") near5 (plasma	USPAT; US-PGPUB;	10:54
		or dry) same clean\$4 and (via or hole or	EPO; JPO;	10.0.
		contact or plug or trench)) not ((NF3 or	DERWENT;	
		"NF.sub.3" or fluor\$4) near10 (o2 or	IBM_TDB	
		oxygen or "o.sub.2") near5 (plasma or	_	
		dry) same clean\$4 same (via or hole or		
		contact or plug or trench)) not (((NF3 or		
		"NF.sub.3") near10 (o2 or oxygen or "o.sub.2") near5 plasma) and (boe or		
		buffer\$3 near2 oxid\$3 near3 etch\$4)) not		
		((NF3 or "NF.sub.3") near10 (o2 or oxygen		
		or "o.sub.2") near5 plasma same clean\$4)		
-	71		USPAT;	2003/06/06
		(o2 or oxygen or "o.sub.2") near5 (plasma	US-PGPUB;	10:56
		or dry) same clean\$4 and (via or hole or	EPO; JPO;	
		contact or plug or trench)) not ((NF3 or "NF.sub.3" or fluor\$4) near10 (o2 or	DERWENT; IBM TDB	
		oxygen or "o.sub.2") near5 (plasma or	1511_100	
		dry) same clean\$4 same (via or hole or		
1		contact or plug or trench)) not (((NF3 or		
		"NF.sub.3") near10 (o2 or oxygen or		
1		"o.sub.2") near5 plasma) and (boe or		
		buffer\$3 near2 oxid\$3 near3 etch\$4)) not ((NF3 or "NF.sub.3") near10 (o2 or oxygen		
		or "o.sub.2") near5 plasma same clean\$4)		
		not (clean\$4 same (boe or buffer\$3 near2		
1		oxid\$2 near2 etch\$4) same	1	
1		("h.sub.2so.sub.4" or h2s04 or sulfuric))		
-	51	(wet same (dry or plasma) same clean\$4	USPAT;	2003/06/06
		same etch\$4 same (via or hole or contact	US-PGPUB;	11:02
1		or plug or residu\$4)).ab.	EPO; JPO; DERWENT;	
1			IBM TDB	
_	113	((NF3 or "NF.sub.3") near10 (o2 or oxygen	USPAT;	2003/06/06
		or "o.sub.2") near5 plasma same etch\$4)	US-PGPUB;	11:34
	1	not ((NF3 or "NF.sub.3") near10 (o2 or	EPO; JPO;	
	1	oxygen or "o.sub.2") near5 plasma same	DERWENT;	
1		clean\$4)	IBM_TDB	2003/06/09
-	38	(NF3 or "Nf.sub.3" or fluor\$4) near20 (02 or "o.sub.2" or oxygen) near5 plasma same	USPAT; US-PGPUB;	15:27
1		(clean\$4) same (via or contact or hole or	EPO; JPO;	13.27
1	1	trench)	DERWENT;	
			IBM TDB	
		<u> </u>		

				1 2 2 2 4 2 4 2 2
-	68	(NF3 or "Nf.sub.3") near20 (o2 or	USPAT;	2003/06/09
		"o.sub.2" or oxygen) near5 plasma same	US-PGPUB;	15:44
		(clean\$4)	EPO; JPO;	
			DERWENT;	
			IBM TDB	
l <u>-</u>	55	dry near10 wet same bak\$4 same clean\$4	USPAT;	2003/06/09
		<u> </u>	US-PGPUB;	18:32
			EPO; JPO;	
			DERWENT;	
·		4 75 1 112 1 00 1 41 10 41	IBM_TDB	2002/06/00
-	22		USPAT;	2003/06/09
		near10 (boe or buffer\$3 near2 oxide near2	US-PGPUB;	18:15
		etch\$4)	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	22	(sulfuric or "H.sub.2So.sub.4" or h2so4)	USPAT;	2003/06/09
		near10 (boe or buffer\$3 near2 oxid\$3	US-PGPUB;	18:27
ŀ		near2 etch\$4)	EPO; JPO;	
		lical 2 cosity 1)	DERWENT;	
l			IBM TDB	
		/1 6d = an HII and OG = 4H hO 4N	_	2002/06/00
-	94	,	USPAT;	2003/06/09
		same (boe or buffer\$3 near2 oxid\$3 near2	US-PGPUB;	18:28
1		etch\$4)	EPO; JPO;	
1			DERWENT;	
1			IBM_TDB	
-	30	(sulfuric or "H.sub.2So.sub.4" or h2so4)	USPĀT;	2003/06/09
1		same (boe or buffer\$3 near2 oxid\$3 near2	US-PGPUB;	18:32
1		etch\$4) same clean\$4	EPO; JPO;	
ľ			DERWENT;	
			IBM TDB	
	1 1	(1-6		2002/06/00
-	8	, , , , , , , , , , , , , , , , , , , ,	USPAT;	2003/06/09
	1	same (boe or buffer\$3 near2 oxid\$3 near2	US-PGPUB;	18:33
		etch\$4) and ("nf3" or "nf.sub.3" or	EPO; JPO;	
	1	nitrogen near2 fluoride)	DERWENT;	
			IBM_TDB	
-	23		USPAT;	2003/06/09
		plasma) same (bak\$4) same semiconduct\$4	US-PGPUB;	18:53
1]		EPO; JPO;	
]		DERWENT;]
]		IBM TDB	
		 wet near10 clean\$4 same plug same dry	USPAT;	2003/07/16
l ⁻	50	wet hearto creansa same brud same dry		· · ·
1			US-PGPUB;	17:49
1			EPO; JPO;	
			DERWENT;	
]		IBM_TDB	
-	33	wet near10 clean\$4 same	USPAT;	2003/07/16
]	("h.sub.2so.sub.4" or h2so4 or sulfuric)	US-PGPUB;	17:58
1	1	and dry near10 clean\$4 and bak\$4 and	EPO; JPO;	
1	1	contact	DERWENT;	
1]		IBM TDB	
l _	1 1	shin.in. and contact same clean\$4 and wet	USPAT;	2003/07/16
I -	1		USPAT; US-PGPUB;	
]	and dry and bak\$4		18:02
			EPO; JPO;	
1			DERWENT;	
1			IBM_TDB	
-	1	shin.in. and contact same clean\$4 same	USPAT;	2003/07/16
		"H.sub.2so.sub.4"	US-PGPUB;	18:03
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	9	shin.in. and contact same clean\$4 same	USPAT;	2003/07/16
"			US-PGPUB;	18:11
		wet		10.11
			EPO; JPO;	
]		DERWENT;	
	1		IBM_TDB	,
-	27	((("nf.sub.3" or nf3) or Nitrogen near2	USPAT;	2003/07/16
	[trifluoride) near30 clean\$4) same	US-PGPUB;	18:29
	1	(contact or via or trench\$4) same plasma	EPO; JPO;	
		same (oxygen or o2 or "o.sub.2")	DERWENT;	
			IBM TDB	
	1	I		

		· · · · · · · · · · · · · · · · · · ·		
-	2	2000100749.pn.	USPAT;	2003/07/16
		•	US-PGPUB;	18:34
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	85	(contact or via or trench) near20 clean\$4	USPAT;	2003/07/16
		<pre>same (combinat\$4 or combin\$4) near10 (dry</pre>	US-PGPUB;	18:41
		or plasma)	EPO; JPO;	
		or prasma,	DERWENT;	
			IBM TDB	
	40	(contact or via or trench) near20 clean\$4	USPAT;	2003/07/16
_	40		US-PGPUB;	18:43
		<pre>same (combinat\$4) near10 (dry or plasma)</pre>	EPO; JPO;	10.43
			DERWENT;	
			IBM_TDB	
-	37	(silicon or si) near4 (single or	USPAT;	2003/07/17
		epitax\$4) same plug same (lpcvd or low	US-PGPUB;	16:53
	1	near4 pressur\$4)	EPO; JPO;	
		-	DERWENT;	
			IBM TDB	
_	28	(silicon or si) near4 (single or	USPĀT;	2003/07/17
1		epitax\$4) near20 selectiv\$5 same (lpcvd	US-PGPUB;	17:07
		or low near4 pressur\$4) near10	EPO; JPO;	
!		temperature	DERWENT;	
		cemperature	IBM TDB	
	3.4	/milimon on mi) moon/ /milimolo on		2003/07/18
-	14	(silicon or si) near4 (single or	USPAT;	
		epitax\$4) near20 selectiv\$5 same (lpcvd	US-PGPUB;	10:39
		or low near4 pressur\$4) near20 torr	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	15	(silicon or si) near4 (single or	USPAT;	2003/07/18
		epitax\$4) same (lpcvd) near20 torr	US-PGPUB;	10:42
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	9	(lpcvd).ti. and silicon near5 (epitax\$4	USPAT;	2003/07/18
		or grow\$4 or deposit\$4) same torr	US-PGPUB;	11:01
		of grows4 of deposits4) same toff	EPO; JPO;	11.01
			DERWENT;	
	4.5	4	IBM_TDB	0000/07/10
-	15	(seg or selective near2 epitax\$4) near15	USPAT;	2003/07/18
		(si or silicon) same (contact or plug or	US-PGPUB;	11:11
		via) and (h2 or "h.sub.2" or hydrogen)	EPO; JPO;	
		near5 bak\$4	DERWENT;	
		•	IBM_TDB	
-	8	combinat\$4 near10 wet near10 dry near10	USPAT;	2003/07/18
	[bak\$4	US-PGPUB;	11:12
]		EPO; JPO;	
			DERWENT;	
]		IBM TDB	
_	9	((bak\$4 or anneal\$4 or rapid near3	USPAT;	2003/07/18
		thermal or heat near2 treat\$4 or rta or	US-PGPUB;	11:17
	1	rtp or ptp) near25 (hydrogen or h2 or	EPO; JPO;	
		"h.sub.2")) near30 combinat\$4 near20	DERWENT;	
		clean\$4	IBM_TDB	2002/07/19
-	5	((bak\$4 or anneal\$4 or rapid near3	USPAT;	2003/07/18
		thermal or heat near2 treat\$4 or rta or	US-PGPUB;	11:18
		rtp or ptp) near25 (hydrogen or h2 or	EPO; JPO;	
		"h.sub.2")) near30 combinat\$4 same	DERWENT;	
1		(contact or plug)	IBM_TDB	
-	41	((bak\$4 or anneal\$4 or rapid near3	USPAT;	2003/07/18
]	thermal or heat near2 treat\$4 or rta or	US-PGPUB;	11:19
]	rtp or ptp) near25 (hydrogen or h2 or	EPO; JPO;	
]	"h.sub.2")) near30 (contact or plug) same	DERWENT;	
1		plasma	IBM TDB	
l -	2	•	USPAT;	2003/07/18
		····	US-PGPUB;	13:01
			EPO; JPO;	
			DERWENT;	
	I		IBM TDB	

_	17	(silicon or si) near10 (select\$4 or	USPAT;	2003/07/18
		selectiv\$4) near5 (epitax\$4 or grow\$4 or	US-PGPUB;	13:17
		deposit\$4) near30 (cone or conical or	EPO; JPO;	
		pyramid\$4)	DERWENT;	
			IBM_TDB	
_	93	(silicon or si) near10 (select\$4 or	USPAT;	2003/07/18
		selectiv\$4) near30 (cone or conical or	US-PGPUB;	13:15
		pyramid\$4)	EPO; JPO;	
		pjiamia ₄ i	DERWENT;	
			IBM TDB	
<u> </u> _	76	((silicon or si) near10 (select\$4 or	USPAT;	2003/07/18
-	, ,	selectiv\$4) near30 (cone or conical or	US-PGPUB;	13:15
		pyramid\$4)) not ((silicon or si) near10	EPO; JPO;	13:13
	1		DERWENT;	
	1	(select\$4 or selectiv\$4) near5 (epitax\$4		
		or grow\$4 or deposit\$4) near30 (cone or	IBM_TDB	
		conical or pyramid\$4))		0000/07/10
-	8		USPAT;	2003/07/18
	1	selectiv\$4) near5 (epitax\$4 or grow\$4 or	US-PGPUB;	17:10
		deposit\$4) near30 (peak)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	105	carrier near5 gas\$4 near20 smooth	USPAT;	2003/07/18
	1		US-PGPUB;	17:25
	i		EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	10	(carrier near5 gas\$4 near20 smooth) same	USPAT;	2003/07/18
	10	CVD	US-PGPUB;	17:24
			EPO; JPO;	- · · - ·
			DERWENT;	
			IBM TDB	
	7	(carrier near5 gas\$4 near20 smooth) same	USPAT;	2003/07/18
-	. '		US-PGPUB;	17:24
		chemical near3 vapor near2 deposit\$4	EPO; JPO;	17.24
			DERWENT;	
	1	5 44 00 114	IBM_TDB	2002/07/10
-	17	, · · · · · · · · · · · · · · · · · · ·	USPAT;	2003/07/18
Ì		flow and CVD	US-PGPUB;	17:27
			EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	0000/07/70
-	68	<u> </u>	USPAT;	2003/07/18
		flow near4 rate	US-PGPUB;	17:33
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	13		USPAT;	2003/07/18
	1	flow near4 rate	US-PGPUB;	17:35
	1		EPO; JPO;	
	1		DERWENT;	
	1		IBM_TDB	
-	34	LPCVD same parameter near10 flow near4	USPAT;	2003/07/18
1	1	rate	US-PGPUB;	18:31
			EPO; JPO;	
	1		DERWENT;	
	1		IBM TDB	
l _	10	((h2so4 or "h.sub.2.so.sub.4" or	USPĀT;	2003/07/18
		sulfuric) near20 clean\$4) same (buffer\$4	US-PGPUB;	18:55
1		near2 oxide or boe)	EPO; JPO;	
1		Healt Oxide of Boe;	DERWENT;	
			IBM TDB	
I	1		TOLI TOD	<u> </u>